

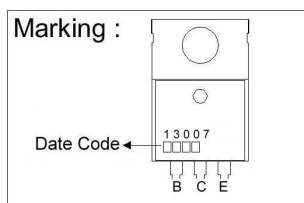
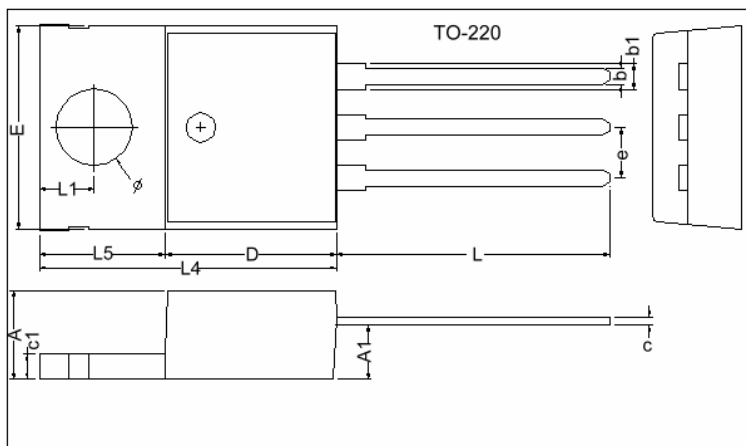
## GE13007

### NPN SILICON TRIPLE DIFFUSED MESA TYPE TRANSISTOR

#### Description

The GE13007 is designed for electronic transformers and power switching circuit applications.

#### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c1	1.25	1.45
b	0.76	1.00	b1	1.17	1.47
c	0.36	0.50	L	13.25	14.25
D	8.60	9.00	e	2.54 REF.	
E	9.80	10.4	L1	2.60	2.89
L4	14.7	15.3	∅	3.71	3.96
L5	6.20	6.60	A1	2.60	2.80

#### Absolute Maximum Ratings at Ta = 25°C

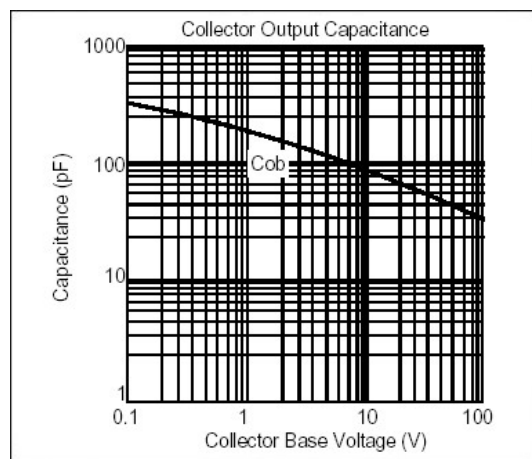
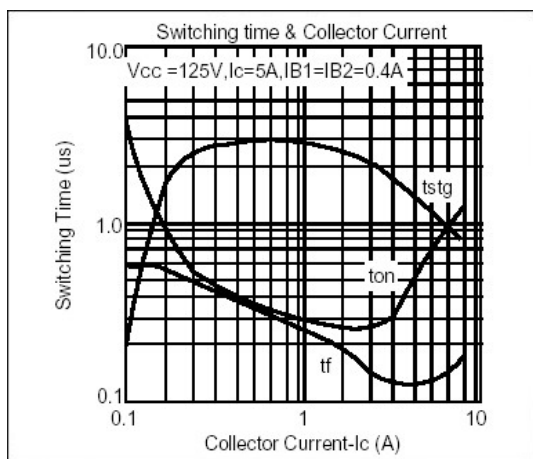
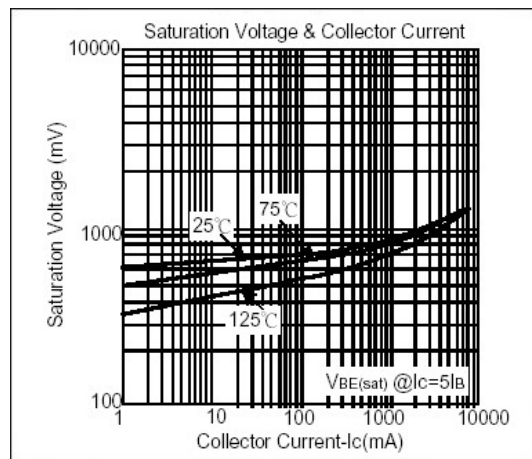
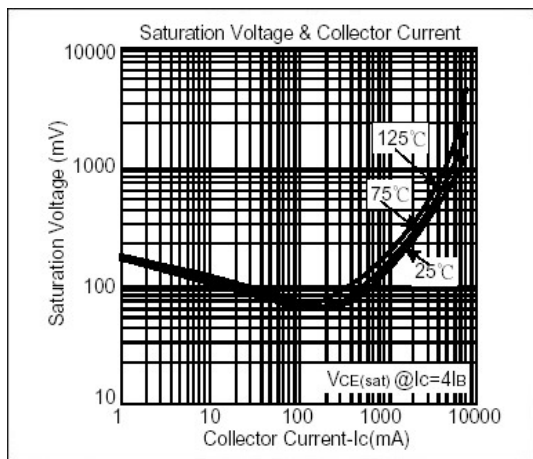
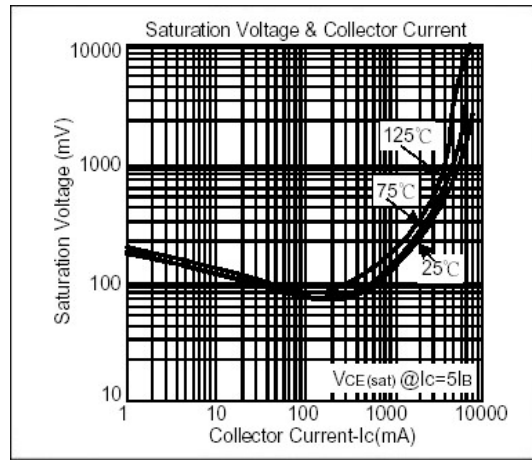
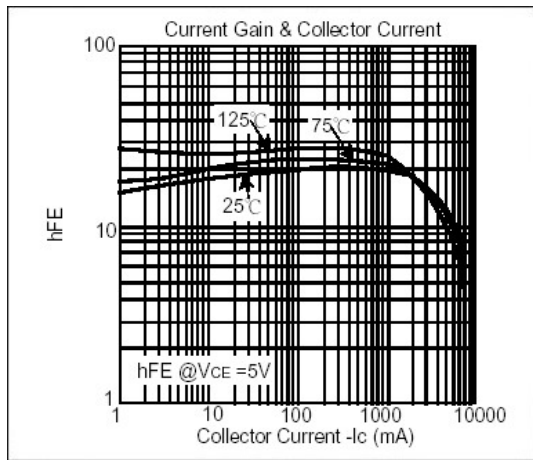
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	700	V
Collector to Emitter Voltage	VCEO	400	V
Emitter to Base Voltage	VEBO	9	V
Collector Current	IC	8	A
Total Power Dissipation at Tc=25°C	PD	80	W

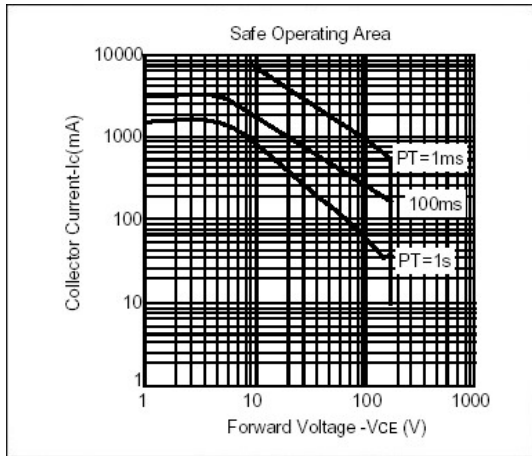
#### Electrical Characteristics(Tc = 25°C Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-Emitter Sustaining Voltage	VCEO(sus)	400	-	-	V	IC=10mA, IB=0
Collector-Base Breakdown Voltage	BVCBO	700	-	-	V	IC=1mA, IE=0
Emitter-Base Breakdown Voltage	BVEBO	9	-	-	V	IE=1mA, IC=0
Collector Cutoff Current	ICBO	-	-	100	μA	VCB=700V
Collector-Emitter Cutoff Current	ICEO	-	-	50	μA	VCE=400V
Emitter-Base Cutoff Current	IEBO	-	-	10	μA	VEB=7V
Collector-Emitter Saturation Voltage	*VCE(sat)1	-	-	1.2	V	IC=2A, IB=400mA
	*VCE(sat)2	-	-	3.0	V	IC=8A, IB=2A
Base-Emitter Saturation Voltage	*VBE(sat)	-	-	1.2	V	IC=2A, IB=400mA
DC Current Gain	*HFE1	8	-	50		VCE=5V, IC=2A
	*HFE2	5	-	-		VCE=5V, IC=5A
Frequency characteristics	fT	4	-	-	MHz	VCE=10V, IC=500mA, f=1MHz
Turn-On Time	ton	-	-	1.6	μs	VCC=125V, IC=5A, IB1=IB2=0.4A
Storage Time	tstg	-	-	3		
Fall Time	tf	-	-	0.7		

\*Pulse Test: Pulse Width=300μs, Duty Cycle ≤ 2%

## Characteristics Curve





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